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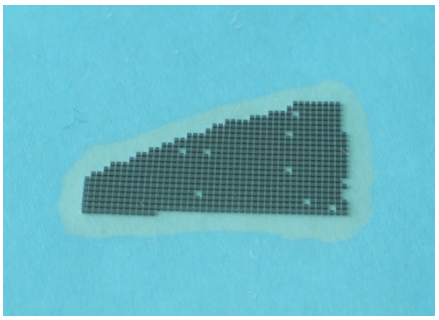
ELC-410-34

- *Violet LED bare chip die*
- *410 nm*
- *5 mW*
- *Sapphire substrate, GAN epi layer*



RoHS COMPLIANT Pb Pb-Free

Description

ELC-410-34 is a bare LED chip die, emitting at 410nm. It is based on Sapphire substrate with an epitaxial layer of GAN based material. P + N electrodes facing up. Chips are delivered on adhesive film with wire-bond side top

Maximum Ratings (T_{amb} = 25°C)

Parameter	Symbol	Values Min.	Values Max.	Unit
Forward Current	I_F		20	mA
Peak Forward Current (tp≤50 µs)	I_{FP}		100	mA

Optical and Electrical Characteristics (T_{CASE} = 25°C, I_F = 20 mA)

Parameter	Symbol	Values Min.	Values Typ.	Values Max.	Unit
Emission Wavelength	λ_{peak}	405	410	415	nm
Spectral Width (FWHM)	$\Delta\lambda$		30		nm
Output Power	P_O	4		6	mV
Operating Voltage	V_F		3.5	3.8	V
Reverse Current	V_R			1	µA

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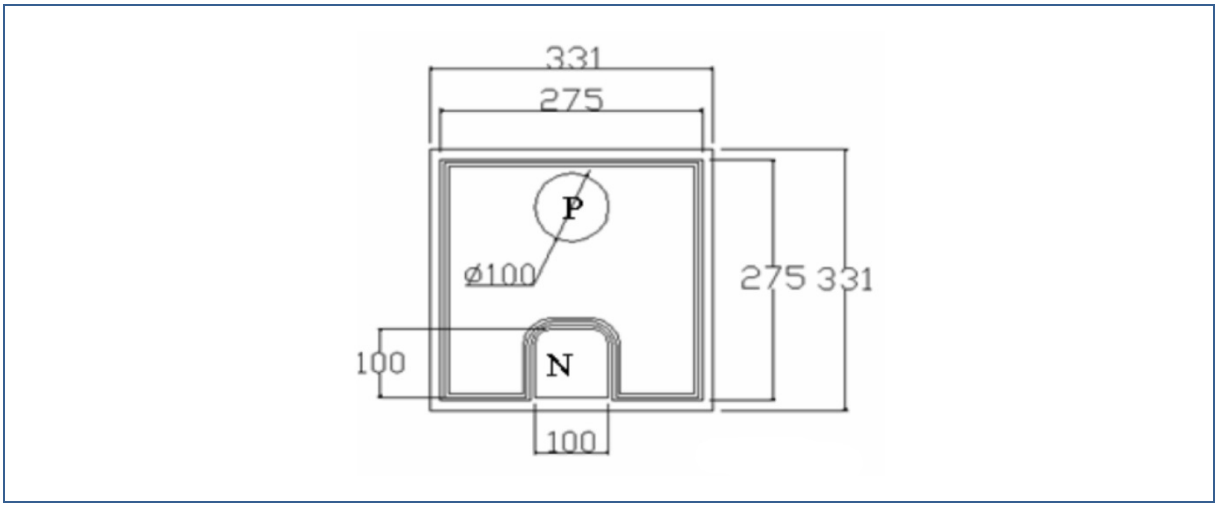
Drawing



Dimensions in µm

Connection

Lead	Material
N pad	AU Alloy
P pad	AU Alloy